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Song et al.

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(54) **METHOD FOR FABRICATING MOS SEMICONDUCTOR DEVICE HAVING SALICIDE REGION AND LDD STRUCTURE**

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(75) Inventors: Oh-Sung Song, Seoul; Ja-Hum Ku, Kyunggi-do, both of (KR)

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(73) Assignee: Samsung Electronics Co., Ltd., Suwon (KR)

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(58) Field of Search 438/305, 529,

438/FOR 188

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Primary Examiner—George Fourson

(74) **Attorney, Agent, or Firm:** Jones Valentine, PLLC

(57) **ABSTRACT**

A method for fabricating a MOS transistor involves forming a buffering layer on an active region, performing an ion implantation to form a heavily doped region (source/drain region), and forming a self-aligned silicide region (salicide region) on exposed silicon and polysilicon gate. With this method, a salicide region free from voids can be formed because transition metal material (for example, cobalt) and silicon atoms at an interface portion between the transition metal layer and the substrate silicon are not locally accelerated or delayed during the formation of the salicide region.

8 Claims, 7 Drawing Sheets

